One Watt High Voltage Transistor

PNP Silicon

Features

• Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V_{CEO}	-300	Vdc
Collector - Base Voltage	V _{CBO}	-300	Vdc
Emitter – Base Voltage	V _{EBO}	-5.0	Vdc
Collector Current - Continuous	I _C	-500	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	P _D	1.0 8.0	W mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	P _D	2.5 20	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

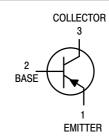
Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	125	°C/W
Thermal Resistance, Junction to Case	$R_{\theta JC}$	50	°C/W

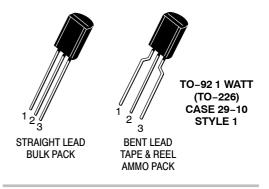
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



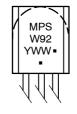
ON Semiconductor®

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MARKING DIAGRAM



MPSW45x = Device Code x = 45A Devices

= Assembly Location

A = Assembl

= Year

WW = Work Week

■ = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

$\textbf{ELECTRICAL CHARACTERISTICS} \ (T_A = 25^{\circ}C \ unless \ otherwise \ noted)$

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS	•		•	
Collector – Emitter Breakdown Voltage (Note 1) $(I_C = -1.0 \text{ mAdc}, I_B = 0)$	V _(BR) CEO	-300	_	Vdc
Collector–Base Breakdown Voltage ($I_C = -100 \mu Adc, I_E = 0$)	V _(BR) CBO	-300	_	Vdc
Emitter–Base Breakdown Voltage $(I_E = -100 \mu Adc, I_C = 0)$	V _{(BR)EBO}	-5.0	_	Vdc
Collector Cutoff Current (V _{CB} = -200 Vdc, I _E = 0)	I _{CBO}	-	-0.25	μAdc
Emitter Cutoff Current (V _{EB} = -3.0 Vdc, I _C = 0)	I _{EBO}	-	-0.1	μAdc
ON CHARACTERISTICS (Note 1)	<u>.</u>			
DC Current Gain $ \begin{aligned} &(I_C = -1.0 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ &(I_C = -10 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \\ &(I_C = -30 \text{ mAdc, } V_{CE} = -10 \text{ Vdc)} \end{aligned} $	h _{FE}	25 40 25	- - -	_
Collector–Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	V _{CE(sat)}	-	-0.5	Vdc
Base–Emitter Saturation Voltage ($I_C = -20$ mAdc, $I_B = -2.0$ mAdc)	V _{BE(sat)}	-	-0.9	Vdc
SMALL-SIGNAL CHARACTERISTICS	•		•	
Current-Gain - Bandwidth Product (I _C = -10 mAdc, V _{CE} = -20 Vdc, f = 20 MHz)	f _T	50	_	MHz
Collector-Base Capacitance (V _{CB} = -20 Vdc, I _E = 0, f = 1.0 MHz)	C _{cb}	-	6.0	pF

^{1.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
MPSW92	TO-92	5000 Units / Box
MPSW92G	TO-92 (Pb-Free)	5000 Units / Box
MPSW92RLREG	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

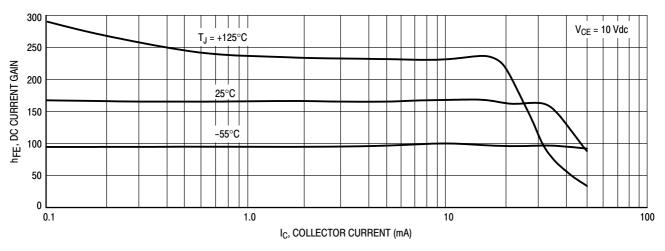


Figure 1. DC Current Gain

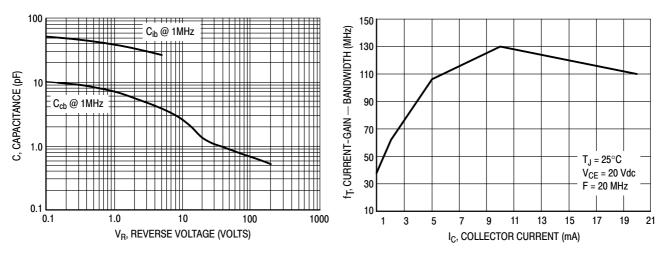
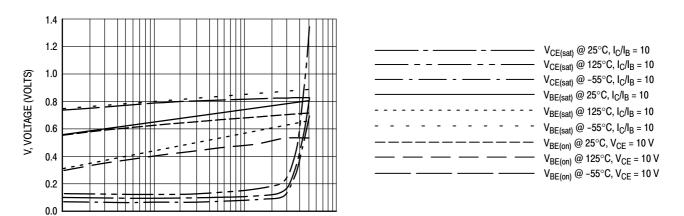


Figure 2. Capacitance



100

Figure 3. Current-Gain - Bandwidth

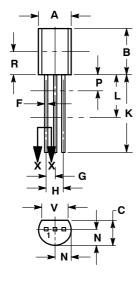
I_C, COLLECTOR CURRENT (mA)

Figure 4. "ON" Voltages

0.1

PACKAGE DIMENSIONS

TO-92 (TO-226) 1 WATT CASE 29-10 **ISSUE O**



STRAIGHT LEAD **BULK PACK**



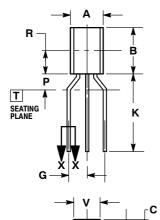
NOTES

- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1994.
 CONTROLLING DIMENSION: INCHES.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
- DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DI-MENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

	INC	INCHES		IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
Н	0.095	0.105	2.42	2.66
ſ	0.018	0.024	0.46	0.61
K	0.500		12.70	
L	0.250	-	6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.135		3.43	
٧	0.135		3.43	

STYLE 1: PIN 1. EMITTER

BASE COLLECTOR



BENT LEAD TAPE & REEL AMMO PACK



NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- CONTROLLING DIMENSION: INCHES.
 CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
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	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.175	0.205	4.44	5.21
В	0.290	0.310	7.37	7.87
С	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500		12.70	
N	0.080	0.105	2.04	2.66
P		0.100		2.54
R	0.135		3.43	
v	0.135		3 43	

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